

# HAT2085T

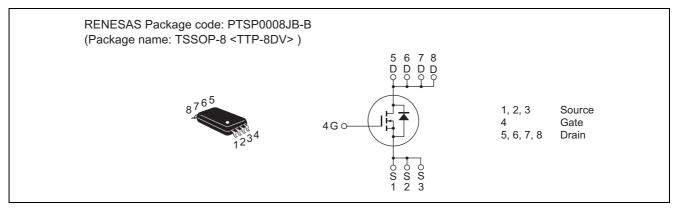
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G0163-0500 Rev.5.00 Nov 27, 2007

# Features

- Low on-resistance
- Low drive current
- High density mounting

# Outline



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Value	Unit
Drain to source voltage	V <sub>DSS</sub>	200	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	1.4	А
Drain peak current	I <sub>D (pulse)</sub> Note 1	11.2	А
Body to drain diode reverse drain current	I <sub>DR</sub>	1.4	Α
Channel dissipation	Pch Note 2	1.3	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

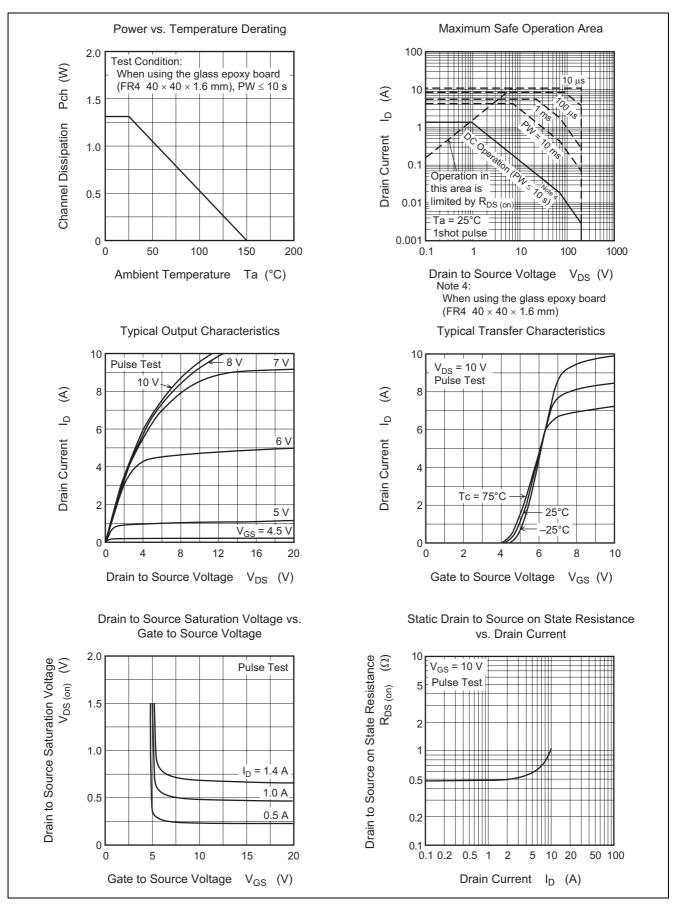
2. When using the glass epoxy board (FR4 40  $\times$  40  $\times$  1.6 mm), PW  $\leq$  10 s

# **Electrical Characteristics**

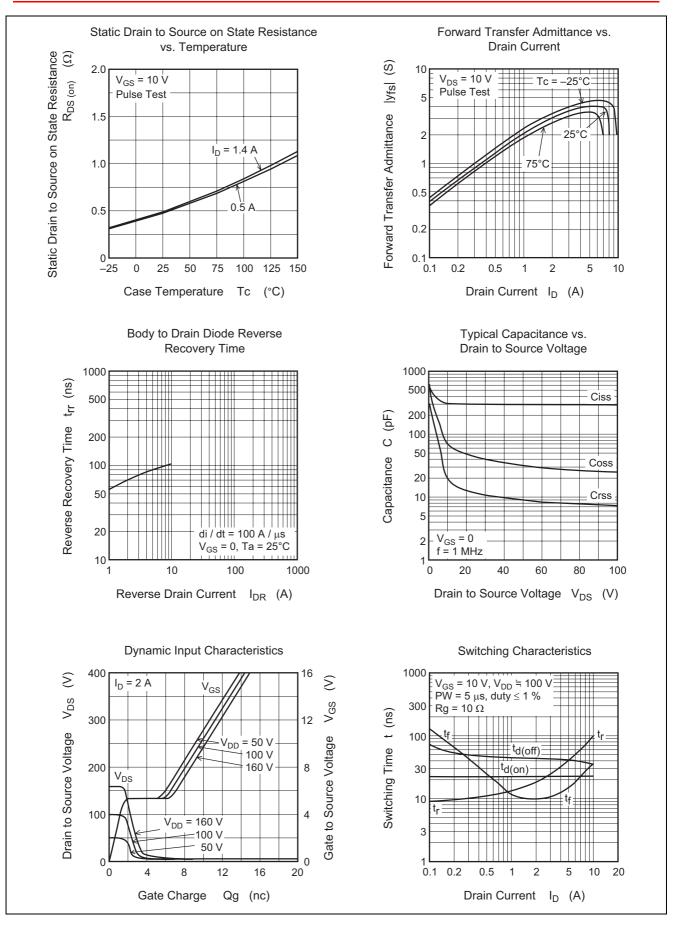
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	V (BR) DSS	200		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	—	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V <sub>GS (off)</sub>	3.0	—	4.5	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	R <sub>DS (on)</sub>	_	0.49	0.64	Ω	$I_D = 0.7 \text{ A}, V_{GS} = 10 \text{ V}^{Note 3}$
Forward transfer admittance	y <sub>fs</sub>	1.0	1.7	_	S	$I_D = 0.7 \text{ A}, V_{DS} = 10 \text{ V}^{Note 3}$
Input capacitance	Ciss	_	300	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	43	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	12	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d (on)</sub>	_	21	_	ns	$V_{DD}\cong 100~V,~I_D=0.7~A$
Rise time	t <sub>r</sub>	_	11	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d (off)</sub>	_	48	_	ns	R <sub>L</sub> = 143 Ω
Fall time	t <sub>f</sub>	_	18	_	ns	Rg = 10 Ω
Total gate charge	Qg	_	10	_	nC	V <sub>DD</sub> = 160 V
Gate to source charge	Qgs	_	1.8	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	4.8	_	nC	I <sub>D</sub> = 1.4 A
Body to drain diode forward voltage	V <sub>DF</sub>		0.8	1.2	V	$I_F = 1.4 \text{ A}, V_{GS} = 0^{\text{Note 3}}$
Body to drain diode reverse recovery time	t <sub>rr</sub>		65		ns	$I_F = 1.4 \text{ A}, V_{GS} = 0$
						di <sub>F</sub> /dt = 100 A/μs

Note: 3. Pulse test

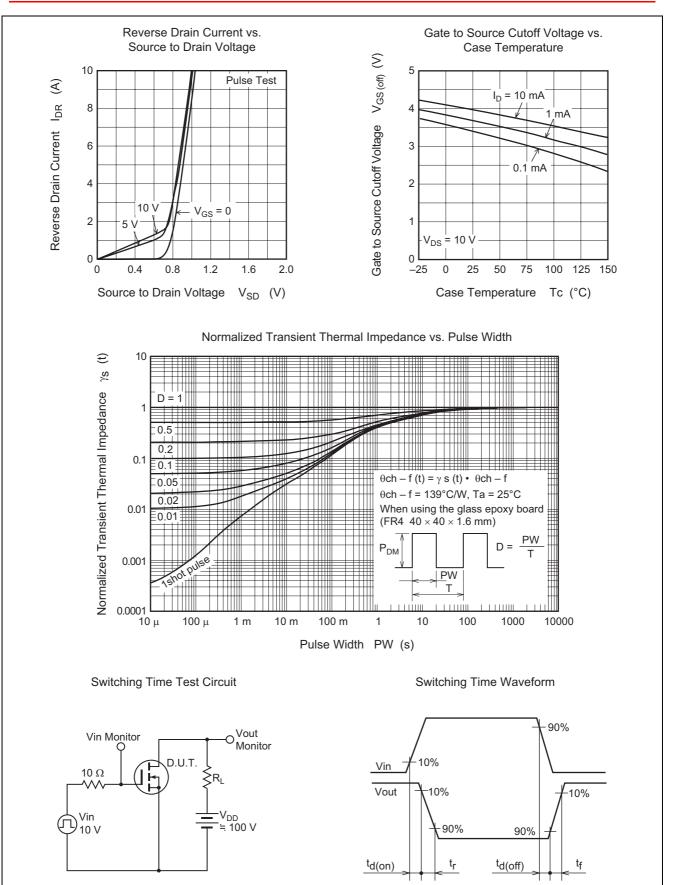
### **Main Characteristics**



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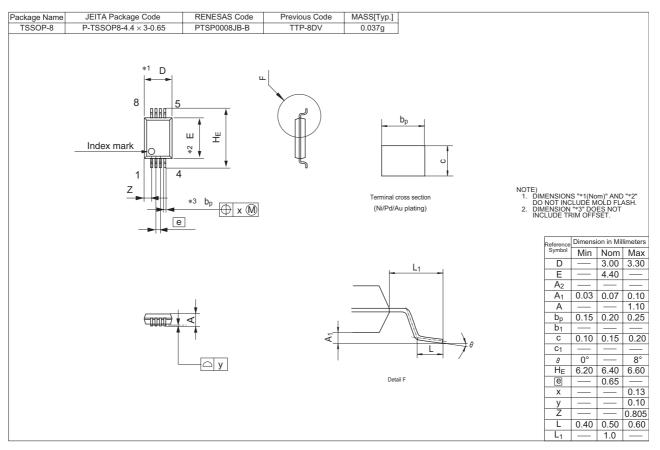


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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2085T-EL-E	3000 pcs	Taping

# RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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